

12.5 Common Source Amplifiers

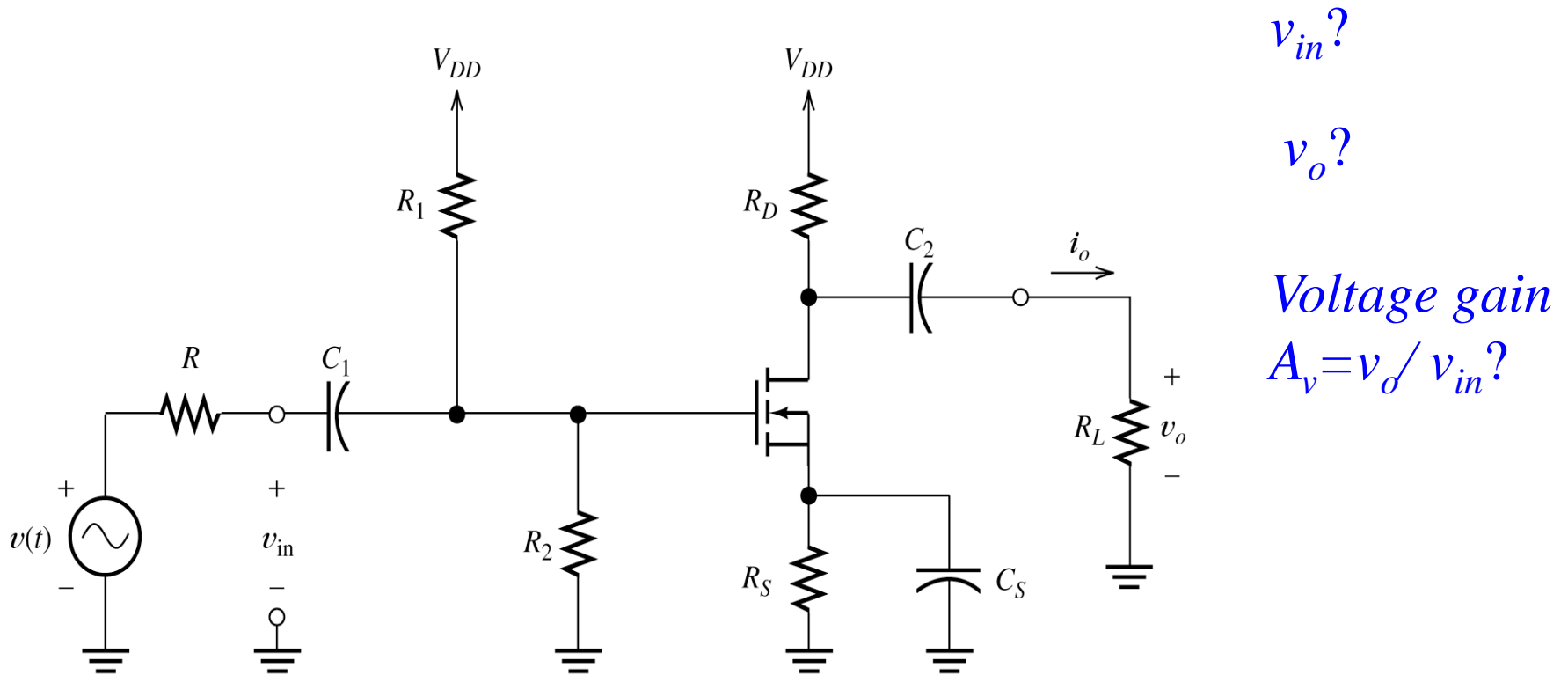


Figure 12.22 Common-source amplifier.

Common-Source Amplifiers

- C_1 and C_2 are coupling capacitors and C_s is the bypass capacitor. The capacitors are intended to have large impedances for the dc signal and very small impedances for the ac signal.

$$Z_c = \frac{1}{j2\pi fC}$$

$$\left\{ \begin{array}{l} Z_c \rightarrow \infty, f = 0 \end{array} \right.$$

$$\left\{ \begin{array}{l} Z_c \rightarrow 0, f \gg 0, \text{ or } C \text{ is large} \end{array} \right.$$

Common-Source Amplifiers

- For DC analysis, the capacitors are replaced by open circuits to determine the quiescent operation point (Q point). The **transconductance** g_m for the small-signal equivalent circuit is also determined.
- For AC analysis, the capacitor are replaced by short circuits to determine the ac voltage gain $A_v = v_o / v_{in}$.

DC Analysis

Coupling capacitors

DC voltage sources

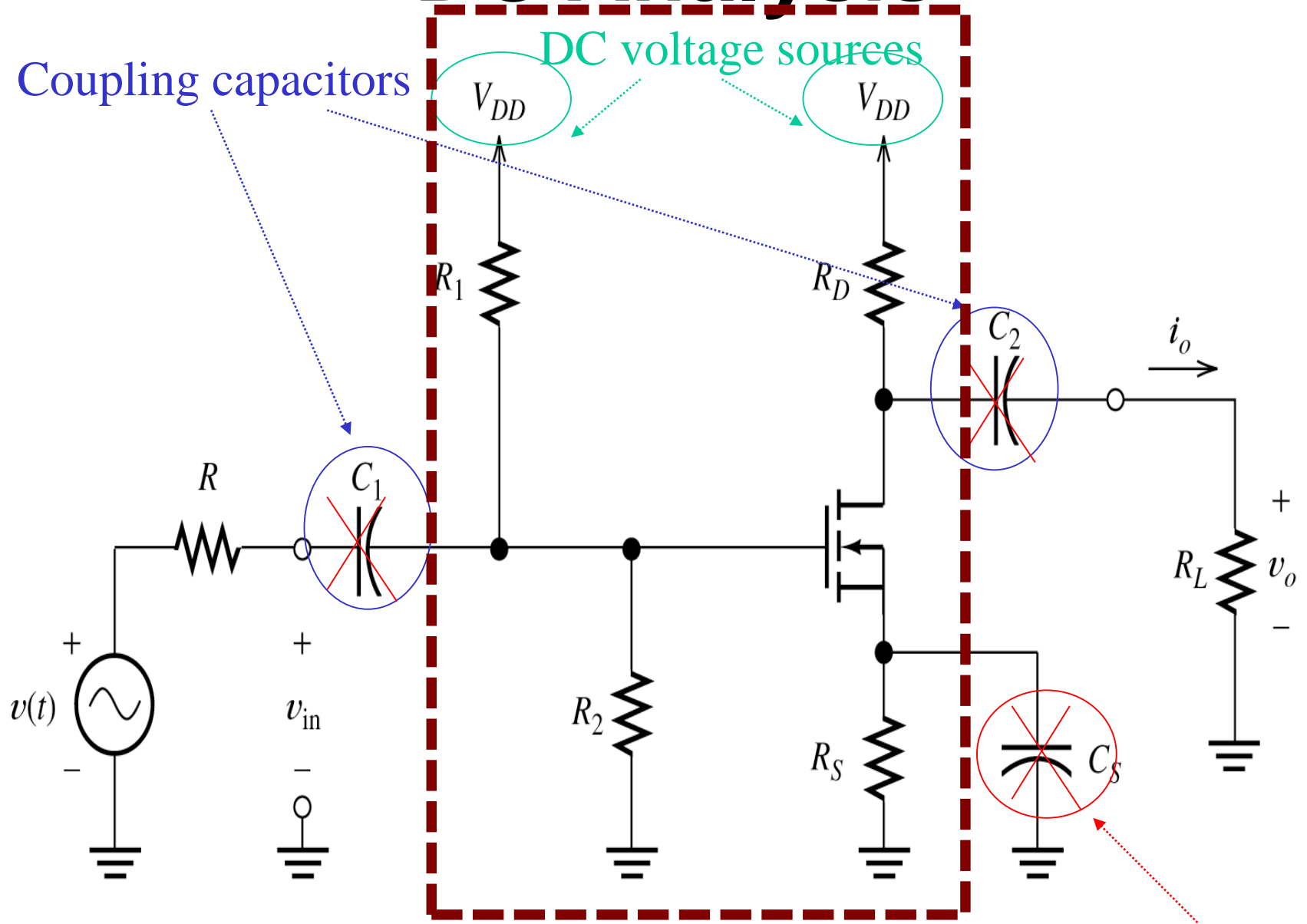


Figure 12.22 Common-source amplifier.

Bypass capacitors

The Small-Signal Equivalent Circuit

- In small-signal midband analysis of FET amplifiers, the coupling capacitors, bypass capacitors, and dc voltage sources are replaced by short circuits.
- The FET is replaced with its small-signal equivalent circuit. Then, we write circuit equations and derive useful expressions for gains, input impedance, and output impedance.

AC Analysis

DC voltage sources

Coupling capacitors

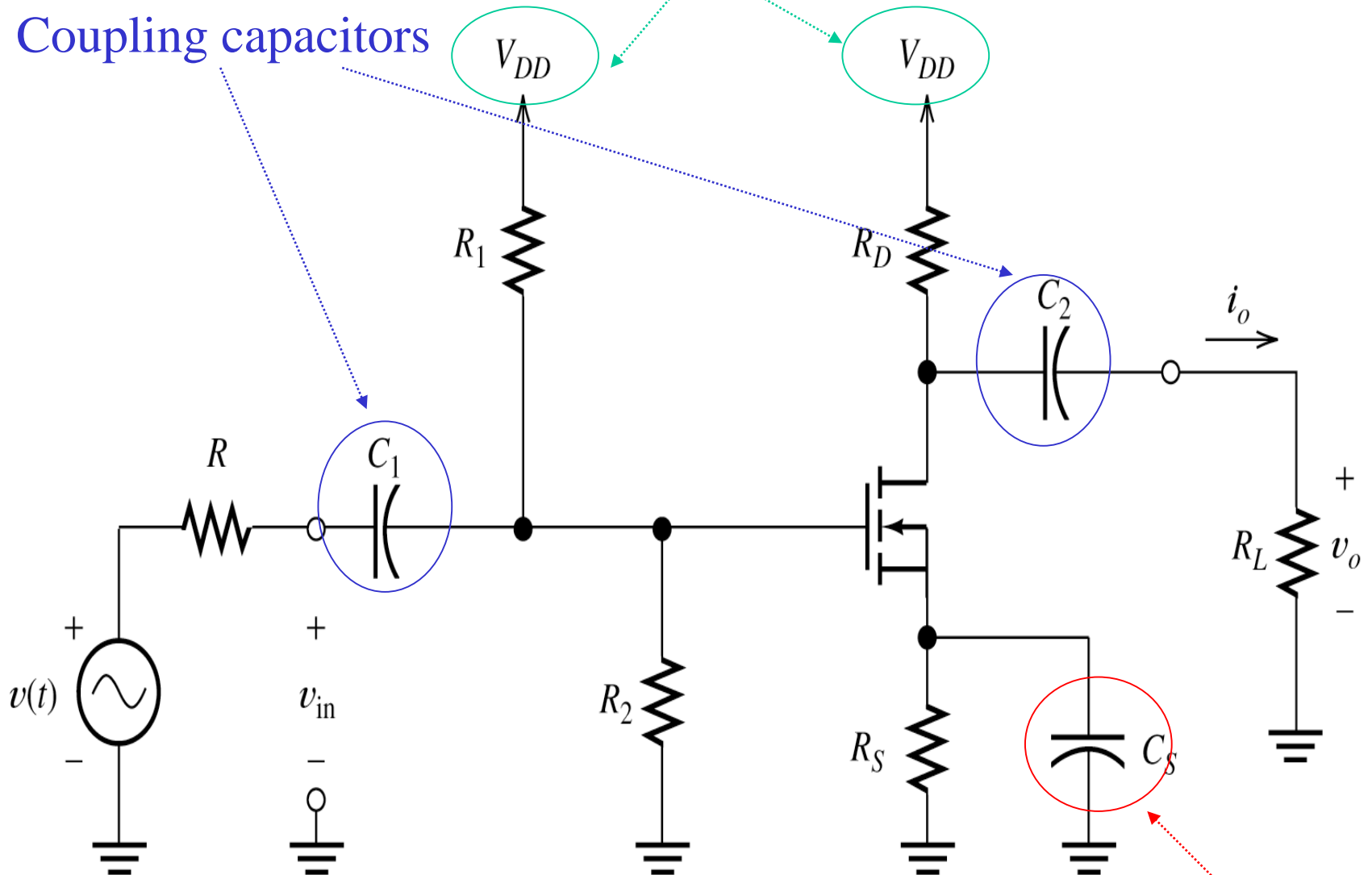


Figure 12.22 Common-source amplifier.

Bypass capacitors

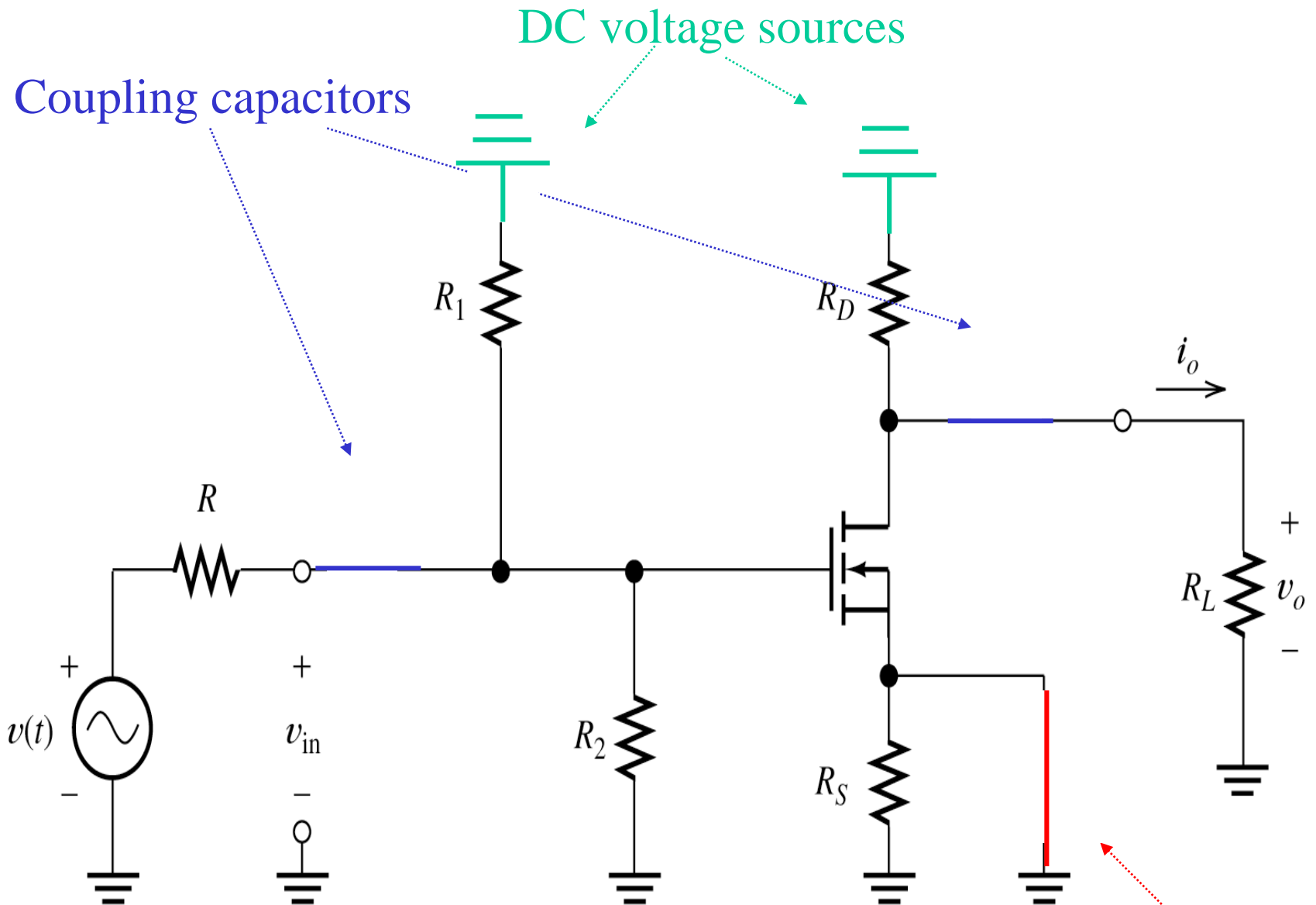
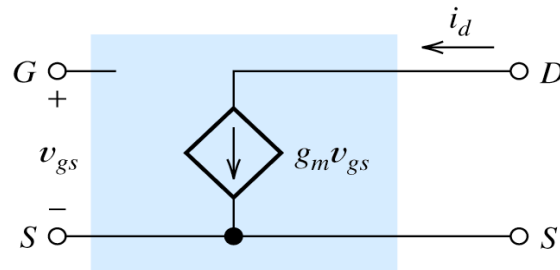
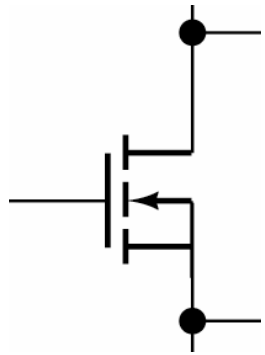


Figure 12.22 Common-source amplifier.

Bypass capacitors

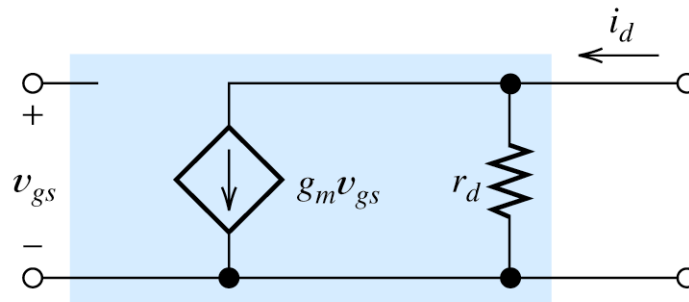
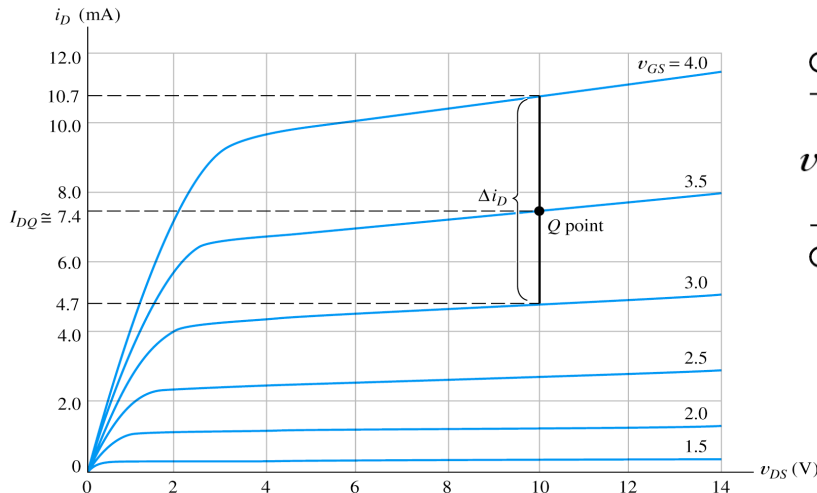
SMALL-SIGNAL EQUIVALENT CIRCUITS (12.4)



$$i_d(t) = g_m v_{gs}(t)$$

Figure 12.19 Small-signal equivalent circuit for FETs.

A more complex equivalent circuit consider **drain resistance r_d**



$$1/r_d = \left. \frac{\partial i_D}{\partial v_{DS}} \right|_{Q\text{-point}}$$

$$i_d(t) = g_m v_{gs}(t) + v_{ds} / r_d$$

Figure 12.21 Determination of g_m and r_d . See Example 12.3.

Common Source Amplifiers: FET source 端接ground

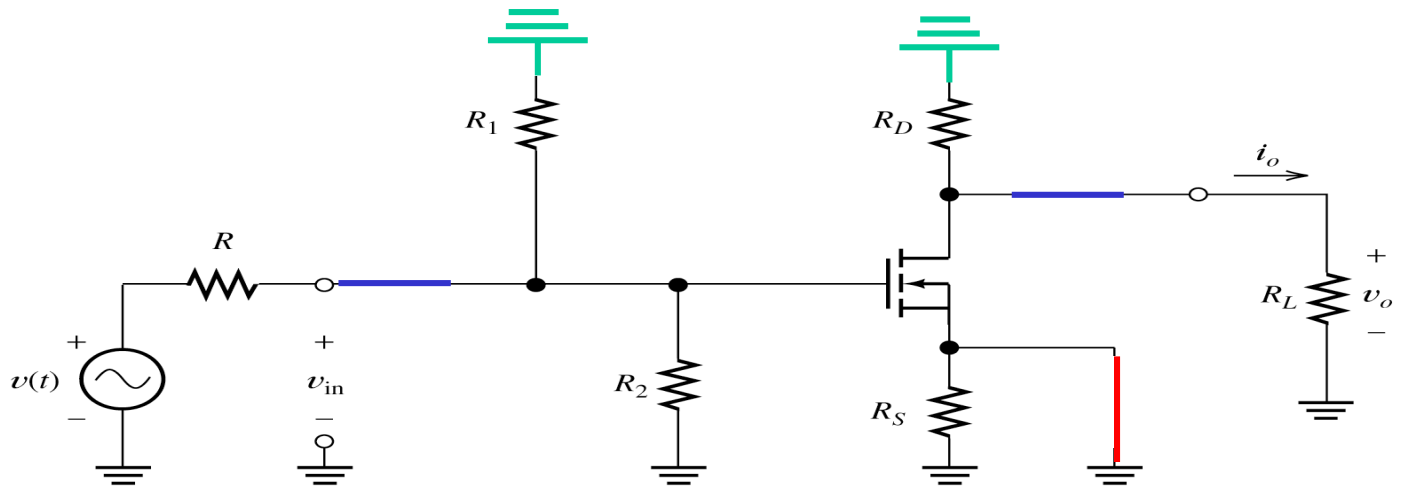


Figure 12.22 Common-source amplifier.

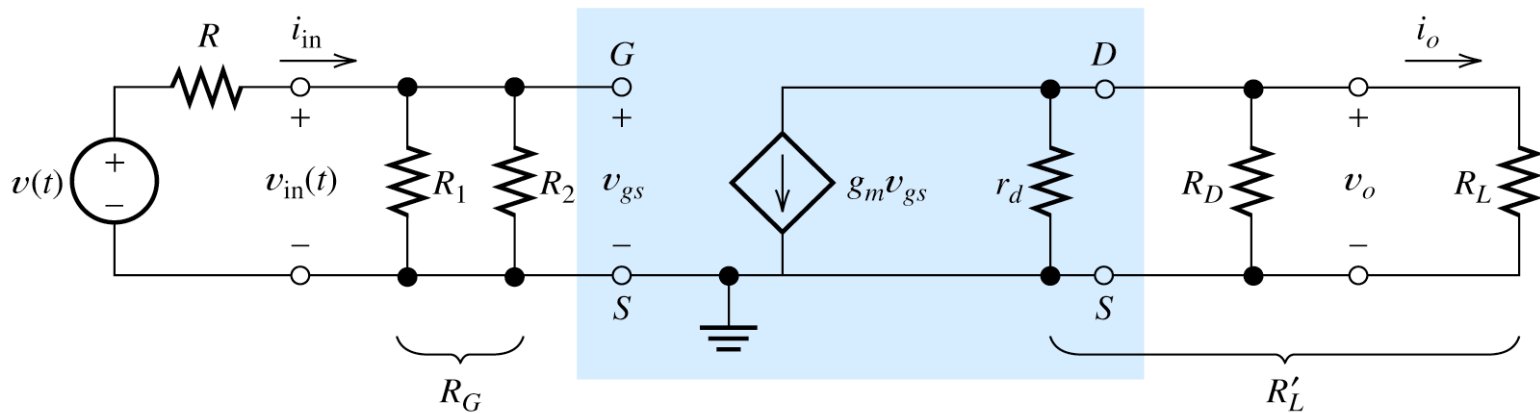


Figure 12.23 Small-signal equivalent circuit for the common-source amplifier.

Common Source Amplifiers:

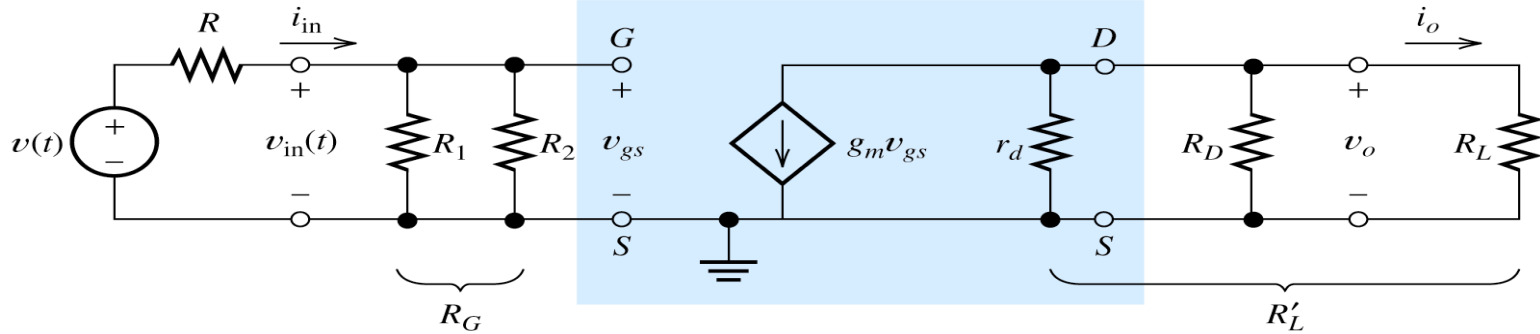


Figure 12.23 Small-signal equivalent circuit for the common-source amplifier.

Equivalent load resistance

$$R'_L = \frac{1}{1/r_d + 1/R_D + 1/R_L}$$

Input voltage & output voltage

$$\begin{cases} v_o = -g_m v_{gs} R'_L \\ v_{in} = v_{gs} \end{cases}$$

Voltage Gain

$$A_v = \frac{v_o}{v_{in}} = -g_m R'_L$$

Common Source Amplifiers:

Input Resistance

$$R_{in} = \frac{v_{in}}{i_{in}} = R_G = R_1 \parallel R_2$$

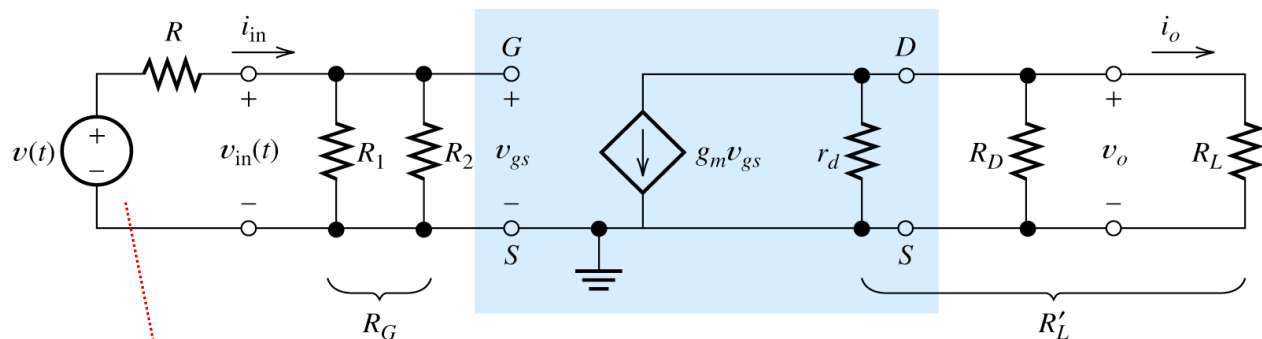


Figure 12.23 Small-signal equivalent circuit for the common-source amplifier.

Output resistance

- disconnect the load,
- replace the signal source by the internal resistance,
- find the resistance by looking into the output terminals.

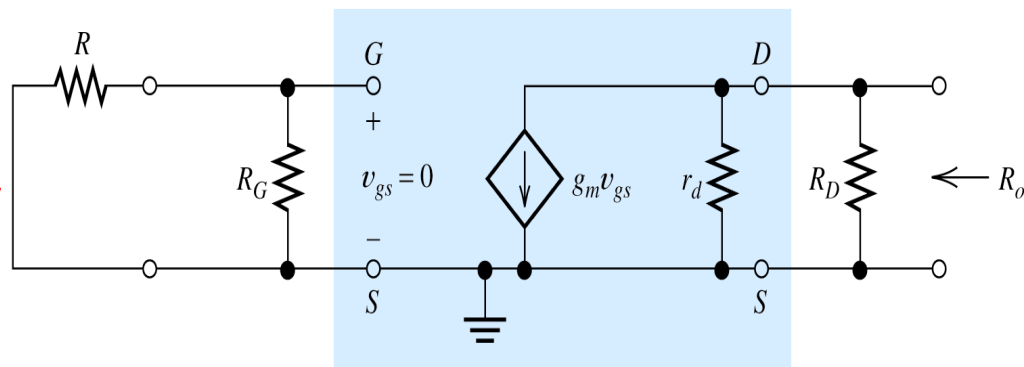


Figure 12.24 Circuit used to find R_o .

$$R_o = \frac{1}{1/R_D + 1/r_d}$$

Example 12.4

Analyze the following circuit. $KP=50\mu\text{A}/\text{V}^2$, $V_{to}=2\text{ V}$, $L=10\mu\text{m}$, $W=400\mu\text{m}$ (identical to example 12.2).

Assume

$$\begin{cases} v(t) = 100 \sin(2000\pi t) \text{ mV} \\ r_d = \infty \end{cases}$$

Find

- midband voltage gain
- input resistance
- output resistance
- output voltage

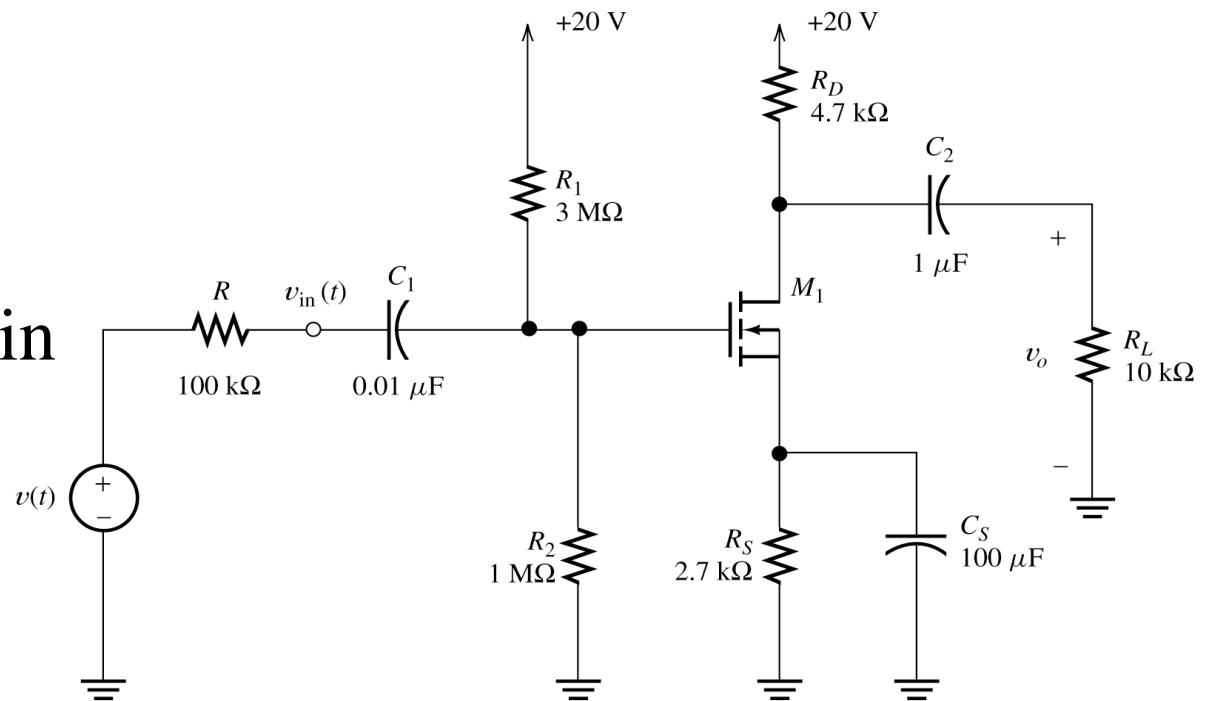


Figure 12.25 Common-source amplifier.

Example 12.4

Analyze the following circuit. $KP=50\mu\text{A}/\text{V}^2$, $V_{to}=2\text{ V}$, $L=10\mu\text{m}$, $W=400\mu\text{m}$ (identical to example 12.2).

DC Analysis

Fine Q point (see example 12.2)

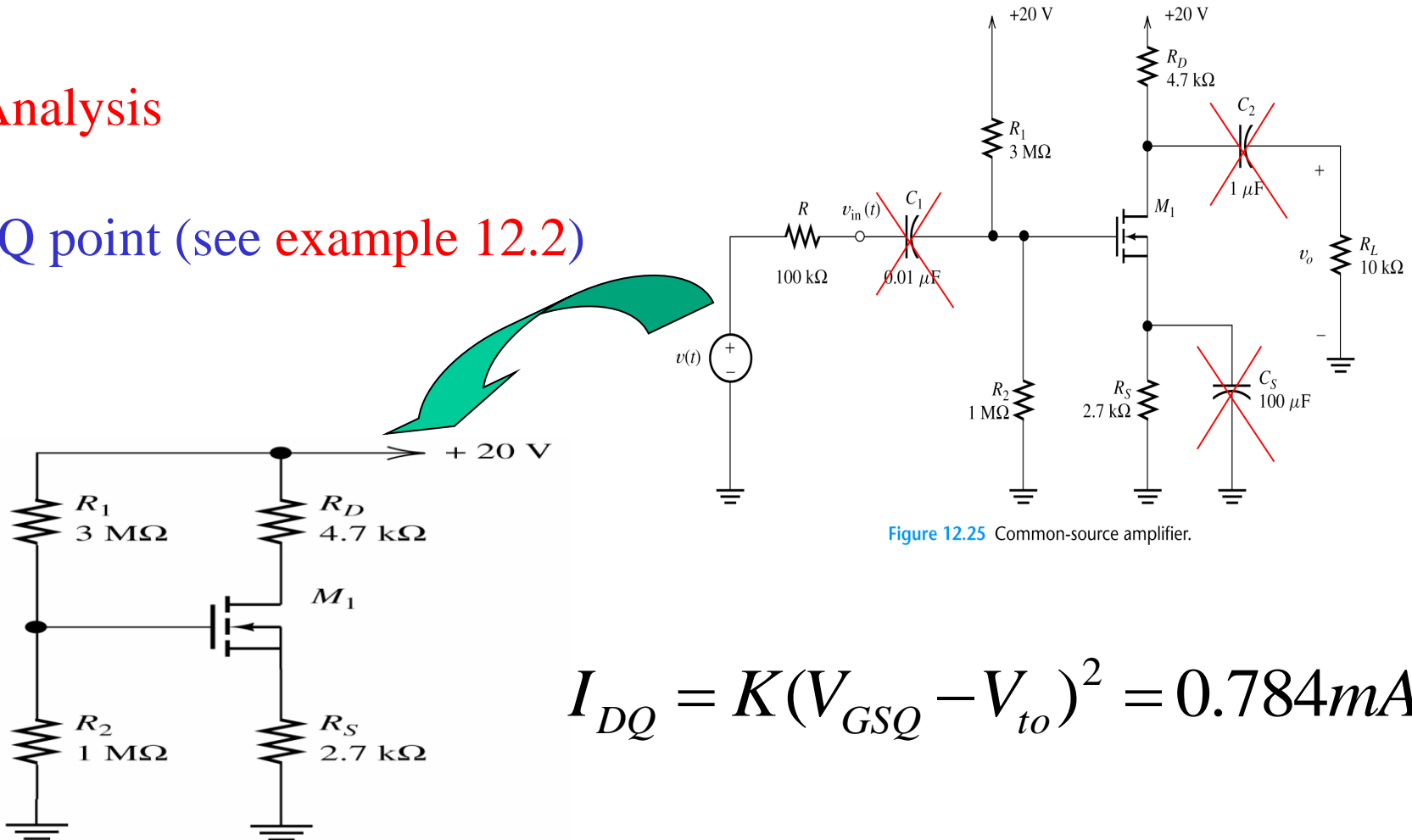


Figure 12.25 Common-source amplifier.

$$I_{DQ} = K(V_{GSQ} - V_{to})^2 = 0.784\text{ mA}$$

Example 12.4

Analyze the following circuit. $KP=50\mu\text{A}/\text{V}^2$, $V_{to}=2\text{ V}$, $L=10\mu\text{m}$, $W=400\mu\text{m}$ (identical to example 12.2).

AC Analysis

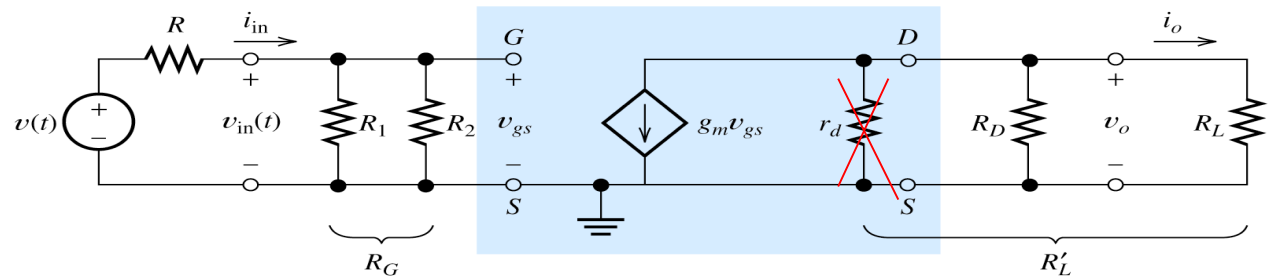


Figure 12.23 Small-signal equivalent circuit for the common-source amplifier.

Fine g_m (see Ch 12.4)

$$g_m = 2K(V_{GSQ} - V_{to}) = \sqrt{2KP} \sqrt{W/L} \sqrt{I_{DQ}} = 1.77\text{ mS}$$

Equivalent load resistance

$$R'_L = \frac{1}{1/\cancel{r_d} + 1/R_D + 1/R_L} = 3197\Omega \quad (r_d = \infty)$$

Voltage Gain

$$A_v = \frac{v_o}{v_{in}} = -g_m R'_L = -5.66$$

Example 12.4

Analyze the following circuit. $KP=50\mu\text{A}/\text{V}^2$, $V_{to}=2\text{ V}$, $L=10\mu\text{m}$, $W=400\mu\text{m}$ (identical to example 12.2).

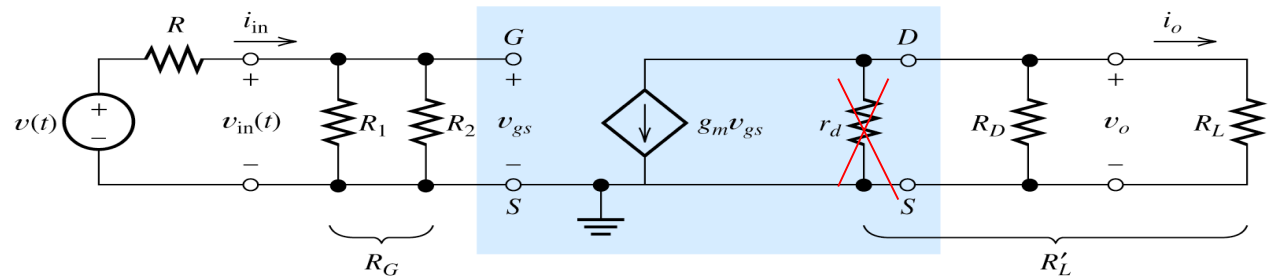


Figure 12.23 Small-signal equivalent circuit for the common-source amplifier.

Input Resistance

$$R_{in} = \frac{v_{in}}{i_{in}} = R_G = R_1 \parallel R_2 = 750\text{k}\Omega$$

Output Resistance

$$R_o = \frac{1}{1/R_D + 1/\cancel{r_d}} = R_D = 4.7\text{k}\Omega$$

Input voltage

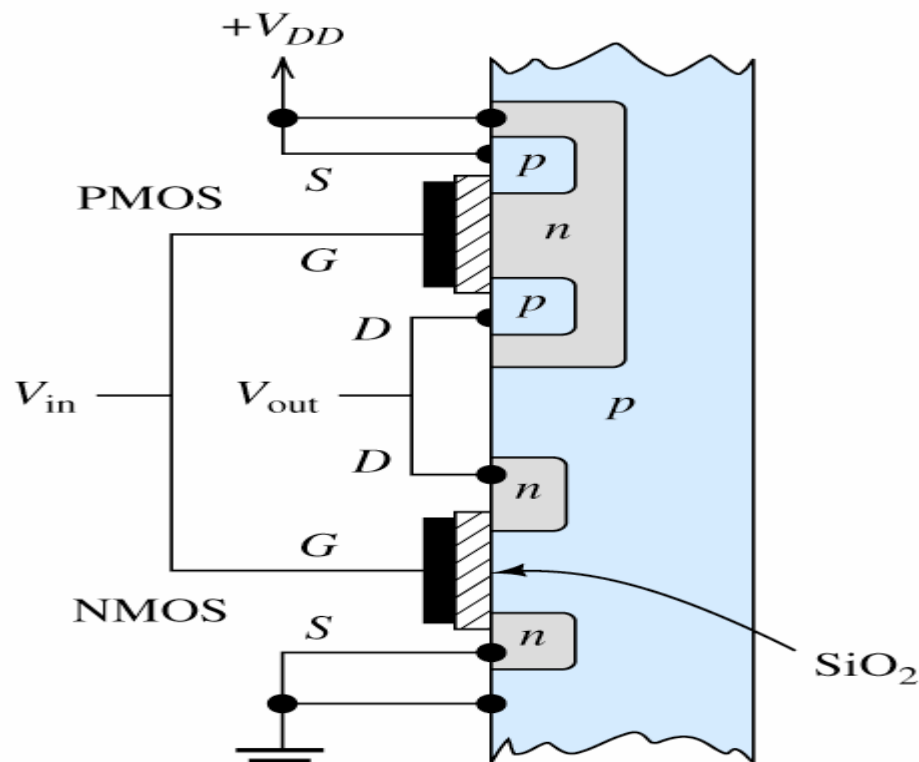
$$v_{in}(t) = v_{gs}(t) = v(t) \frac{R_{in}}{R_{in} + R} = 88.23 \sin(2000\pi t) \text{ mV}$$

Output voltage

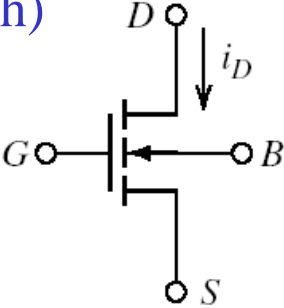
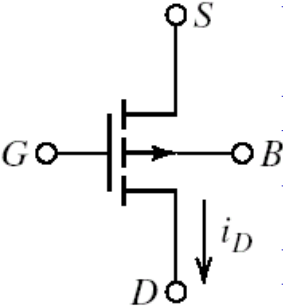
$$v_o(t) = A_v v_{in}(t) = -500 \sin(2000\pi t) \text{ mV}$$

12.7 CMOS Logic Gate

CMOS: **Complementary Metal-Oxide-Semiconductor** (互補式金氧半導體是一種積體電路製程，可在矽晶圓上製作出 PMOS (P-channel MOSFET) 和 NMOS (N-channel MOSFET) 元件，由於 PMOS 與 NMOS 在特性上為互補性，因此稱為 CMOS。



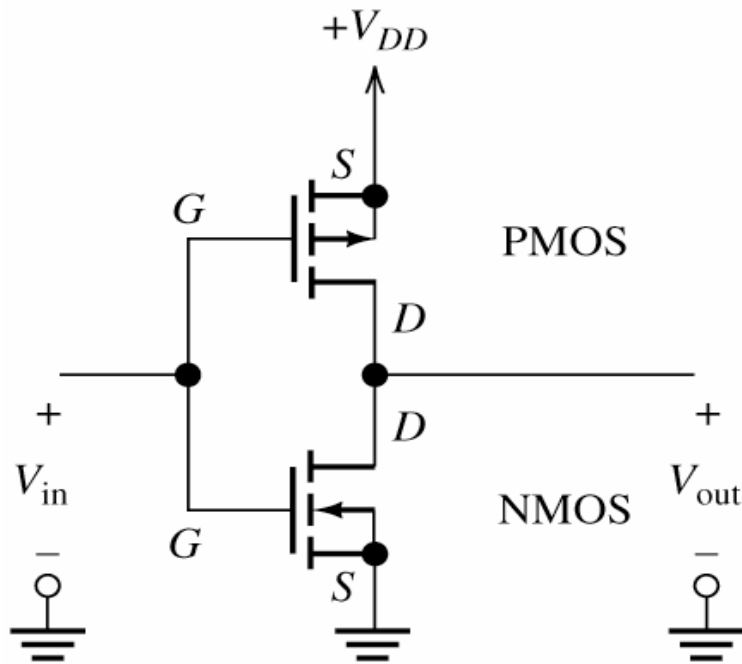
MOSFET Summary

	NMOS	PMOS
Circuit symbol $V_{GS}=V_{DD}$ (high) NMOS ON $V_{GS}=0$ (low) NMOS OFF		 $V_{GS}=V_{DD}$ PMOS ON $V_{GS}=0$ PMOS OFF
KP (typical value)	$50 \mu A/V^2$	$25 \mu A/V^2$
K	$(1/2) KP (W/L)$	$(1/2) KP (W/L)$
V_{to} (typical value)	+1 V	-1 V
Cutoff region	$v_{GS} \leq V_{to}$ $i_D = 0$	$v_{GS} \geq V_{to}$ $i_D = 0$
Triode region	$v_{GS} \geq V_{to}$ and $0 \leq v_{DS} \leq v_{GS} - V_{to}$ $i_D = K [2(v_{GS} - V_{to}) v_{DS} - v_{DS}^2]$	$v_{GS} \leq V_{to}$ and $0 \geq v_{DS} \geq v_{GS} - V_{to}$ $i_D = K [2(v_{GS} - V_{to}) v_{DS} - v_{DS}^2]$
Saturation region	$v_{GS} \geq V_{to}$ and $v_{DS} \geq v_{GS} - V_{to}$ $i_D = K (v_{GS} - V_{to})^2$	$v_{GS} \leq V_{to}$ and $v_{DS} \leq v_{GS} - V_{to}$ $i_D = K (v_{GS} - V_{to})^2$
v_{DS} and v_{GS}	Normally assume positive values	Normally assume negative values

CMOS Inverter

NMOS $V_{GS} = V_{in}$

PMOS $V_{GS} = V_{in} - V_{DD}$



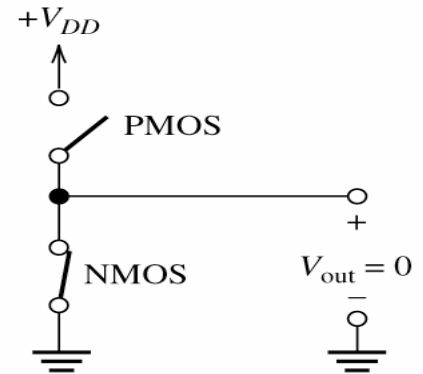
(b) Circuit diagram

$V_{in} = V_{DD}$ (high)

NMOS $V_{GS} = V_{DD}$ ON,

PMOS $V_{GS} = 0$ OFF,

$V_{out} = 0$ (low)



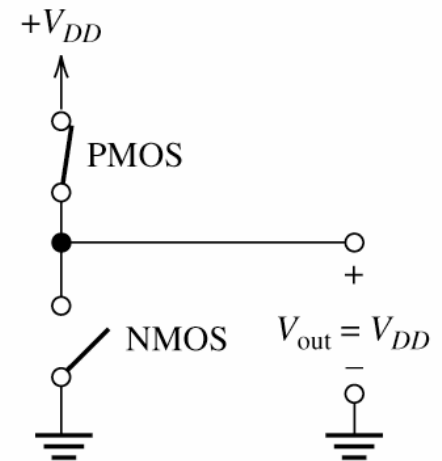
(c) Equivalent circuit with V_{in} high

$V_{in} = 0$ (low)

NMOS $V_{GS} = 0$ OFF

PMOS $V_{GS} = -V_{DD}$ ON,

$V_{out} = V_{DD}$ (high)



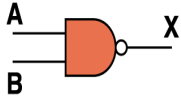
(d) Equivalent circuit with V_{in} low

CMOS NAND Gate

Boolean Expression

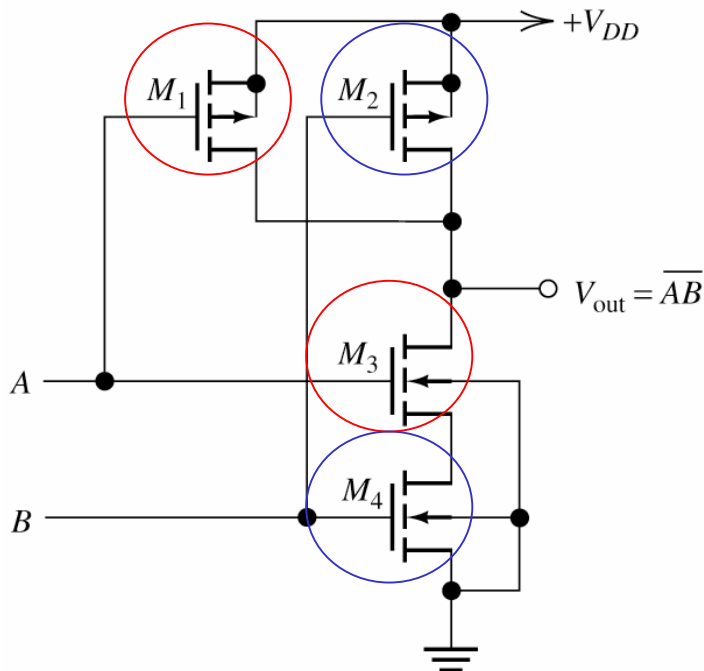
$$X = (A \cdot B)'$$

Logic Diagram Symbol



Truth Table

A	B	X
0	0	1
0	1	1
1	0	1
1	1	0



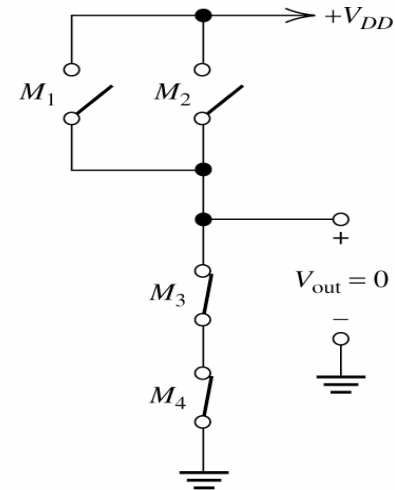
(a) Circuit diagram

1. A= high & B= high

M1 and M2 OFF

M3 and M4 ON

V_{out} low



(c) Both A and B are high

2. A= low & B= low

M1 and M2 ON

M3 and M4 OFF

V_{out} high

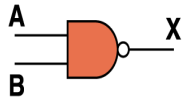
CMOS NAND Gate

Boolean Expression

Logic Diagram Symbol

Truth Table

$$X = (A \cdot B)'$$



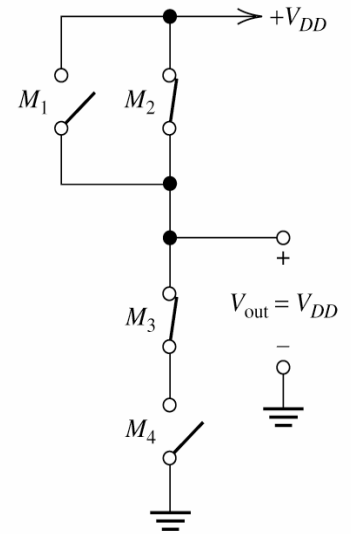
A	B	X
0	0	1
0	1	1
1	0	1
1	1	0

3. A= high & B= low

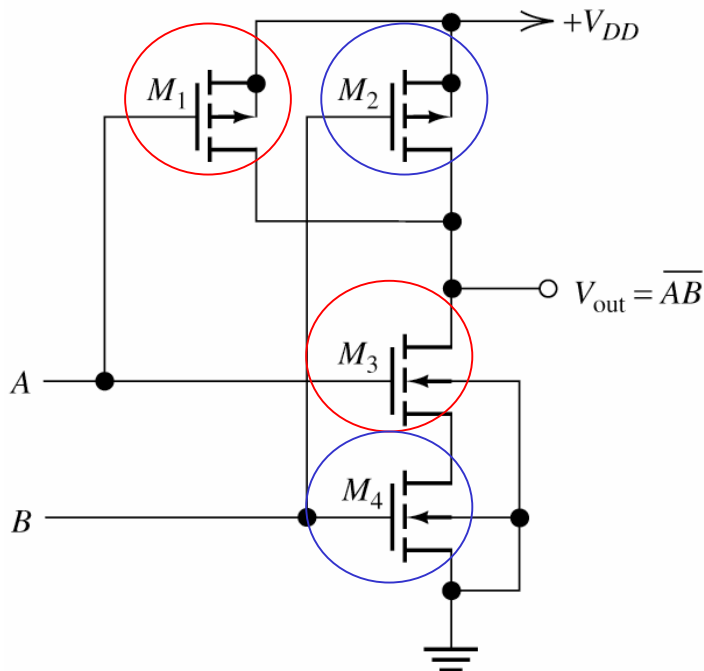
M1 OFF and M2 ON

M3 ON and M4 OFF

V_{out} high



(b) A high and B low



(a) Circuit diagram

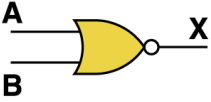
4. A= low & B= high

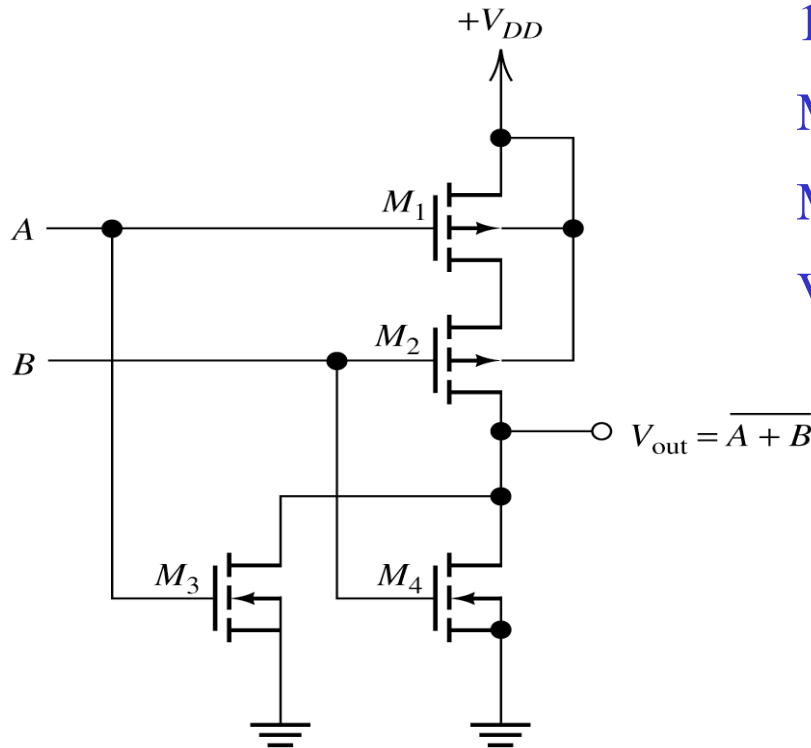
M1 ON and M2 OFF

M3 OFF and M4 ON

V_{out} high

CMOS NOR Gate

Boolean Expression	Logic Diagram Symbol	Truth Table															
$X = (A + B)'$		<table> <tr> <th>A</th><th>B</th><th>X</th></tr> <tr> <td>0</td><td>0</td><td>1</td></tr> <tr> <td>0</td><td>1</td><td>0</td></tr> <tr> <td>1</td><td>0</td><td>0</td></tr> <tr> <td>1</td><td>1</td><td>0</td></tr> </table>	A	B	X	0	0	1	0	1	0	1	0	0	1	1	0
A	B	X															
0	0	1															
0	1	0															
1	0	0															
1	1	0															



1. A= low & B= low

M1 and M2 ON

M3 and M4 OFF

V_{out} high

3. A= high & B= high

M1 and M2 OFF

M3 and M4 ON

V_{out} low

2. A= high & B= low

M1 and M4 OFF

M2 and M3 ON

V_{out} low

Figure 12.33 Two-input CMOS NOR gate.